





	<p>SI2342DS-T1-GE3</p>
	<p>Hersteller-Teilenummer: SI2342DS-T1-GE3</p> <p>Hersteller / Marke: Vishay / Spectrol</p> <p>Teil der Beschreibung: MOSFET N-CH 8V 6A SOT-23</p> <p>Datenblätter:  SI2342DS-T1-GE3.pdf</p> <p>RoHs Status: Bleifrei / RoHS-konform</p> <p>Lagerzustand: New original, 156815 pcs Stock Available.</p> <p>Liefern von: Hong Kong</p> <p>Versandweg: DHL/Fedex/TNT/UPS/EMS</p>
<p>Image may be representation. See specs for product details.</p>	

Spezifikationen

Teilenummer	SI2342DS-T1-GE3
Hersteller	Vishay / Spectrol
Beschreibung	MOSFET N-CH 8V 6A SOT-23
Kategorie	Diskrete Halbleiterprodukte > Transistoren-FETs,
Teilstatus	156815 pcs Stock
Hersteller-Teilenummer	SI2342DS-T1-GE3
Beschreibung	MOSFET N-CH 8V 6A SOT-23
Feuchtigkeitsempfindlichkeitsstufe (MSL)	1 (Unlimited)
Hersteller Standard Vorlaufzeit	24 Weeks
Expanded Beschreibung	N-Channel 8V 6A (Tc) 1.3W (Ta), 2.5W (Tc) Surface
RoHS Status	Tape & Reel (TR)
Serie	TrenchFET®
Technologie	MOSFET (Metal Oxide)
Betriebstemperatur	-55°C ~ 150°C (TJ)
Befestigungsart	Surface Mount
Polarisation	TO-236-3, SC-59, SOT-23-3
Spannung - Durchschlag	SOT-23
Kapazitätsverhältnis	1.3W (Ta), 2.5W (Tc)
FET-Merkmal	N-Channel
Drain-Source-Spannung (Vdss)	-
Strom - Ununterbrochener Abfluss (Id) bei 25 ° C	8V
Rds On (Max) @ Id, Vgs	6A (Tc)
VGS (th) (Max) @ Id	17 mOhm @ 7.2A, 4.5V
Gate Charge (Qg) (Max) @ Vgs	800mV @ 250µA
Eingabekapazität (Ciss) (Max) @ Vds	15.8nC @ 4.5V
Spannung - Prüfung	1070pF @ 4V
Vgs (Max)	1.2V, 4.5V
IGBT-Typ	±5V
Andere Namen	SI2342DS-T1-GE3-ND




































SI2342DS-T1-GE3 ist neu im Original, Suche SI2342DS-T1-GE3 Datenblätter, PDF, Inventar bei Y-IC.com Online, Bestellen Sie SI2342DS-T1-GE3 Vishay / Spectrol mit Garantie und Vertrauen. Anfrage SI2342DS-T1-GE3: Info@Y-IC.com

Sie können auch interessiert sein:

 <p>SI2343CDS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 5.9A SOT-23</p>	 <p>SI2343CDS VISHAY SI2343CDS VISHAY</p>	 <p>SI2342DS-T1-GE3 Vishay / Siliconix MOSFET N-CH 8V 6A SOT-23</p>	 <p>SI2343CDS-T1-E3 VISHAY SI2343CDS-T1-E3 VISHAY</p>
 <p>SI2343ADS-T1-GE3 V SI2343ADS-T1-GE3 V</p>	 <p>SI2341DS-T1-GE3 Electro-Films (EFI) / Vishay MOSFET P-CH 30V 2.5A SOT-23</p>	 <p>SI2343CDS-T1-GE3 Vishay / Siliconix MOSFET P-CH 30V 5.9A SOT-23</p>	 <p>SI2341DS-T1-E3 Vishay / Siliconix MOSFET P-CH 30V 2.5A SOT-23</p>

heiße Teile

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|  SI2334DS-T1-E3 |  SI2334DS-T1-GE3 |  SI2334DS-T1-GE3 | D SI2335DS-T1 |  SI2335DS-T1-E3 |
|  SI2335DS-T1-E3 |  SI2335DS-T1-GE3 | D SI2335DS-T1-GE3 |  SI2336DS-T1-E3 |  SI2336DS-T1-GE3 |
|  SI2336DS-T1-GE3 |  SI2337DS |  SI2337DS-T1-E3 |  SI2337DS-T1-E3 |  SI2337DS-T1-GE3 |
| D SI2337DS-T1-GE3 |  SI2338DS-T1-E3 |  SI2338DS-T1-GE3 |  SI2338DS-T1-GE3 |  SI2341DS |
|  SI2341DS-T1-E3 |  SI2341DS-T1-E3 |  SI2341DS-T1-GE3 |  SI2341DS-T1-GE3 |  SI2342DS-T1-E3 |
|  SI2342DS-T1-GE3 |  SI2343ADS-T1-GE3 | D SI2343CDS |  SI2343CDS-T1-E3 |  SI2343CDS-T1-GE3 |
|  SI2343CDS-T1-GE3 | D SI2343DS-T1-E3 |  SI2343DS-T1-E3 |  SI2343DS-T1-GE3 |  SI2343DS-T1-GE3 |
|  SI2344DS-E3 |  SI2347DS-T1-GE3 |  SI2347DS-T1-GE3 |  SI2351DS-T1-E3 |  SI2351DS-T1-E3 |
|  SI2351DS-T1-GE3 |  SI2351DS-T1-GE3 |  SI2356DS-T1-GE3 | D SI2356DS-T1-GE3 |  SI2365EDS |
|  SI2365EDS-T1-GE3 |  SI2365EDS-T1-GE3 |  SI2366DS-T1-E3 |  SI2366DS-T1-GE |  SI2366DS-T1-GE3 |

